or in part rather than by the foregoing description. All changes that come within the meaning and range of equivalency of the claims are to be embraced within their scope. --

IN THE CLAIMS:

Please cancel claims 21-28.

Please amend the following claims:

1. (Thrice Amended) A semiconductor structure comprising:

an electrically conductive interconnect disposed within a first dielectric layer, said electrically conductive interconnect having an upper surface;

a passivation layer disposed upon said upper surface, said passivation layer comprising nitrogen adsorbed upon said upper surface according to Brunauer's Type V adsorption; and

an interlayer dielectric disposed upon said first dielectric layer and upon said upper surface, said interlayer dielectric being continuously adhered to said upper surface.

7. (Thrice Amended) A semiconductor structure comprising:

an electrically conductive interconnect having an upper surface and being disposed within a dielectric layer, said electrically conductive interconnect including:

a titanium liner layer disposed within a depression in said dielectric layer;

a titanium nitride layer disposed upon said titanium liner layer; and

a tungsten film disposed upon said titanium nitride layer and filling said depression;

a first passivation layer comprising a tungsten nitride compound and being disposed upon said upper surface,

a second passivation layer comprising multiple layers of nitrogen compounds adsorbed upon said first passivation layer according to Brunauer's Type V adsorption; and

an interlayer dielectric disposed upon said dielectric layer and upon said upper surface, said interlayer dielectric being continuously adhered to said upper surface.

8. (Thrice Amended) A semiconductor structure comprising:

an electrically conductive interconnect disposed within a dielectric layer, said electrically conductive interconnect having an upper surface and including:

a titanium liner layer disposed within a depression in said dielectric layer;

a titanium nitride layer disposed upon said titanium liner layer; and

a tungsten film disposed upon said titanium nitride layer and filling said depression;

a passivation layer disposed upon said upper surface and comprising nitrogen adsorbed upon said upper surface according to Brunauer's Type V adsorption; and

an interlayer dielectric disposed upon said dielectric layer and upon said upper surface, said interlayer dielectric being continuously adhered to said upper surface.

9. (Thrice Amended) An interconnect in an electronic device comprising:

a metallic first structure disposed within a first silicon oxide layer, said metallic first structure having an upper surface;

a passivation layer disposed upon said upper surface, said passivation layer formed by exposing said upper surface to a plasma consisting essentially of a nitrogen-containing silane; and

a second silicon oxide layer disposed upon said first silicon oxide layer and upon said upper surface, said second silicon oxide layer being continuously adhered to said upper surface.

15. (Thrice Amended) An interconnect in an electronic device comprising:

a metallic structure disposed within a first silicon oxide layer, said metallic structure having an upper surface and including:

a titanium liner layer disposed within an interconnect corridor in said first silicon oxide layer;

a titanium nitride layer disposed upon said titanium liner layer; and

a tungsten film disposed upon said titanium nitride layer;

a first passivation layer disposed upon said upper surface and comprised of a tungsten nitride compound;

a second passivation layer consisting essentially of a nitrogen-containing silane disposed upon said first passivation layer; and

a second silicon oxide layer disposed upon said first silicon oxide layer and upon said upper surface, said second silicon oxide layer being continuously adhered to said upper surface.

16. (Thrice Amended) An interconnect in an electronic device comprising:

a metallic structure disposed within a first silicon oxide layer, said metallic structure having an upper surface and including:

a titanium liner layer disposed within an interconnect corridor in said first silicon oxide layer;

a titanium nitride layer disposed upon said titanium liner layer; and

a tungsten film disposed upon said titanium nitride layer;

a passivation layer disposed upon said upper surface and consisting essentially of a nitrogen-containing silane; and

a second silicon oxide layer disposed upon said first silicon oxide layer and upon said upper surface, said second silicon oxide layer being continuously adhered to said upper surface.

17. (Twice Amended) A semiconductor structure comprising:

an electrically conductive interconnect disposed within a first dielectric layer, said electrically conductive interconnect having an upper surface;

a first passivation layer disposed upon said upper surface, said first passivation layer comprising a tungsten nitride compound;

a second passivation layer comprising multiple layers of nitrogen compounds adsorbed upon said first passivation layer according to Brunauer's Type V adsorption; and

an interlayer dielectric disposed upon said first dielectric layer and upon said upper surface, said interlayer dielectric being continuously adhered to said upper surface.

19. (Twice Amended) An interconnect in an electronic device comprising:

a metallic first structure disposed within a first silicon oxide layer, said metallic first structure having an upper surface;

a first passivation layer disposed upon said upper surface, said first passivation layer comprising a tungsten nitride compound;

a second passivation layer comprising multiple layers of nitrogen compounds adsorbed upon said first passivation layer according to Brunauer's Type V adsorption; and

a second silicon oxide layer disposed upon said first silicon oxide layer and upon said upper surface, said second silicon oxide layer being continuously adhered to said upper surface.

29. (Once Amended) A semiconductor structure comprising:

an electrically conductive interconnect disposed within a first dielectric layer, said electrically conductive interconnect having an upper surface;

a passivation layer disposed upon said upper surface, said passivation layer consisting essentially of a nitrogen-containing silane; and

an interlayer dielectric disposed upon said first dielectric layer and upon said upper surface, said interlayer dielectric being continuously adhered to said upper surface.

30. (Once Amended) A semiconductor structure comprising:

an electrically conductive interconnect disposed within a first dielectric layer, said electrically conductive interconnect having an upper surface;

a first passivation layer upon said upper surface, said first passivation layer comprising a tungsten nitride compound;

a second passivation layer upon said first passivation layer, said second passivation layer consisting essentially of a nitrogen-containing silane; and

an interlayer dielectric disposed upon said first dielectric layer and upon said upper surface, said interlayer dielectric being continuously adhered to said upper surface.